PNP General Purpose Transistor multicomp



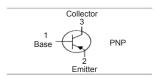


Features:

- Epitaxial planar die construction.
- Complementary NPN type available (MMST5551).
- Also available in lead free version.

Applications:

· Ideal for medium power amplification and switching.





SOT-323

Maximum Rating @ TA = 25°C unless otherwise specified

Parameter	Symbol	Value	Units	
Collector-Base Voltage	V _{CBO}	-160		
Collector-Emitter Voltage	VCEO	-150	V	
Emitter-Base Voltage	V _{EBO}	-5]	
Collector Current (DC)	Ic	-0.6	А	
Collector Dissipation	Pc	0.2	W	
Thermal resistance ,Junction to ambient	RөJA	625	°C/W	
Junction and Storage Temperature	Tj,Tstg	-55 to 150	°C	

Electrical Characteristics @ TA = 25°C unless otherwise specified

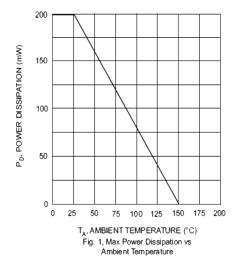
Parameter	Symbol	Test conditions	MIN.	MAX.	UNIT
Collector-Base Breakdown Voltage	V _{(BR)CBO}	Ic = -100μA, IE = 0	-160		
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	Ic = -1mA, IB = 0	-150		
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	IE = -10μA, IC = 0	-5		
Collector Cut-Off Current	Ісво	IE = 0; VCB = -120V		-50	υ.Λ
Emitter Cut-Off Current	I _{EBO}	IC = 0; VEB = -3V	-	-50	nA
DC Current Gain	h _{FE}	VCE = -5V; IC = -1mA VCE = -5V; IC = -10mA VCE = -5V; IC = -50 mA	50 60 50	- 240 -	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	Ic = -50 mA; IB = -5mA Ic = -10mA; IB = -1mA		-0.5 -0.2	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	IC = -50mA; IB = -5mA IC = -10mA; IB = -1mA	-	-1 -1	V
Transition Frequency	fτ	IC = -10mA; VCE = -10V, f = 100MHz	100	300	MHz
Noise Figure	NF	IC = -200mA, VCE = -5V, f = 100MHz		8	dB

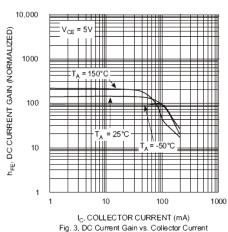
www.element14.com www.farnell.com www.newark.com

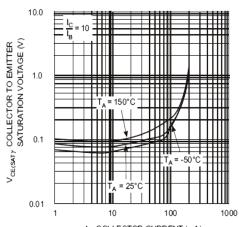


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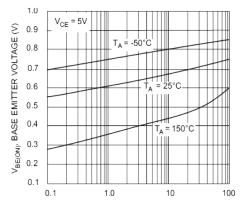
Typical Characteristics @ TA = 25°C unless otherwise specified



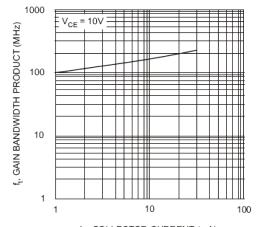




I_C, COLLECTOR CURRENT (mA) Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current



I_C, COLLECTOR CURRENT (mA)
Fig. 4, Base Emitter Voltage vs. Collector Current



I_C, COLLECTOR CURRENT (mA)
Fig. 5, Gain Bandwidth Product vs Collector Current

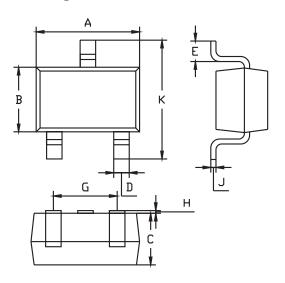




PNP General Purpose Transistor multicomp

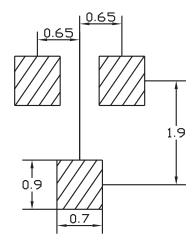


Package Outline



SOT-323				
Dim	Min	Max		
Α	1.8	2.2		
В	1.15	1.35		
С	1Typical			
D	0.15	0.35		
E	0.25	0.40		
G	1.2	1.4		
Н	0.02	0.1		
J	0.1Typical			
K	2.1	2.3		
All Dimensions in mm				

Soldering Footprint



Dimensions: Millimetres

Part Number Table

Description	Part Number		
Transistor, Bipolar, PNP, -150V, -600mA, SOT-323	MMST5401-7-F		

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